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Docket No.: 042390.P11362

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Brian S. Doyle

Application No.: 09/895,579

Filed: June 29, 2001

For: CREATION OF HIGH MOBILITY  
CHANNELS IN THIN-BODY SOI  
DEVICES

Examiner: David Nhu

Art Group: 2818

AMENDMENT AND RESPONSE TO THE OFFICE ACTION

Box Non-Fee Amendment  
Assistant Commissioner for Patents  
Washington, DC 20231-9998

Sir:

In response to the Notice of Non-Compliant Amendment mailed October 25, 2002 and the final Office Action mailed May 1, 2002, please amend the above-identified Application as follows:

IN THE SPECIFICATION

Please replace the heading on page 1, line 6, with the following rewritten heading:

-- DESCRIPTION OF THE RELATED ART --

Please replace the paragraph beginning on page 3, line 11, with the following rewritten paragraph:

-- The relaxed SiGe layer 102 is formed upon or deposited on top the silicon substrate 101. The strained silicon layer 104 is then formed on the relaxed SiGe layer 102. In one embodiment, the relaxed SiGe layer 102, and the strained silicon layer 104 are